

LDMOS AND CMOS INTEGRATED CIRCUIT AND METHOD OF MAKING

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ABSTRACT OF THE DISCLOSURE

An integrated circuit (IC) is formed on a substrate. The IC has a first well having a first dopant concentration that includes a second conductivity low-voltage transistor. The IC also has a second well having a dopant concentration equal to the first dopant concentration that includes a first conductivity high-voltage transistor. In addition, the IC has a third well having a second dopant concentration of an opposite type than the first well that includes a first conductivity low-voltage transistor. The first conductivity low-voltage transistor and the second conductivity low-voltage transistor are created without a threshold voltage (V_t) implant.

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